



MAIL STOP PCT

IFW

Docket No. 291520US0PCT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Kazuhito YASUDA, et al.

SERIAL NO: 10/580,833

GAU:

FILED: May 26, 2006

EXAMINER:

FOR: SEMICONDUCTOR RADIATION DETECTOR AND PROCESS FOR PRODUCING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Norman F. Oblon

Registration No. 24,618

Customer Number

22850

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/03)

Surinder Sachar

Registration No. 34,423

Form PTO 1449
(Modified)DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
291520US0PCTSERIAL NO.
10/580,833

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT
Kazuhito YASUDA, et al.FILING DATE
May 26, 2006

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AT	NAKANISHI, Yutaro et al., "Growth and Electronic Properties of Thick CdTe Layers Grown on GaAs by MOVPE", Technical Report of IEICE., Vol. 103, No. 50, pgs. 81-85, 2003.				
	AU	MASUDA, Yusuke et al., "Arsenic Doping in CdTe Layers Grown by Metalorganic Vapor Phase Epitaxy", Technical Report of IEICE., Vol. 101, No. 82, pgs. 13-18, 2001.				
	AV	YASUDA, K. et al., "MOVPE growth of (100) CdZnTe Layers Using DiPZn", Journal of Crystal Growth, Vol. 159, pgs. 121-125, 1996.				
	AW	UCHIDA, Kei et al., "Study on Detector for Detecting Large Images of Both CdTe- x Ray and Y Ray by Using MOVPE", Dai 64 Kai Extended Abstracts, the Japan Society of Applied Physics, No. 1, pg. 245, 2003 (With Partial English Translation)				
	AX	WANG, Wen-Sheng et al., "(100) or (111) Heteroepitaxy of CdTe Layers on (100) GaAs Substrates by Organometallic Vapor Phase Epitaxy", Materials Chemistry and Physics, Vol. 51, pgs. 178-181, 1997.				
	AY	LEO, G. et al., "Influence of a ZnTe Buffer Layer on the Structural Quality of CdTe Epilayers Grown on (100) GaAs by Metalorganic Vapor Phase Epitaxy", J.Vac.Technol.B., Vol. 14, No. 3, pgs 1739-1744, 1996.				
	AZ				<input type="checkbox"/> Additional References sheet(s) attached	

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.